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(71) Applicant: Hitachi Chemical Company, Ltd.
Tokyo 163-0449 (JP)

(72) Inventors:

• TANAKA, Toshiaki
Tsukuba-shi, Ibaraki 300-3261 (JP)

• DOHDOH, Takafumi
Chiba 299-0114 (JP)
• KITAKATSU, Tsutomu
Ichihara-shi, Chiba 290-0037 (JP)
• KANEDA, Atsou
Yokohama-shi, Kanagawa 245-0053 (JP)
• YASUDA, Masaaki, Hitachi Chemical
Tsukuba-shi, Ibaraki 305-0035 (JP)
• KOUSAKA, Takashi, Hitachi Chemical
Tsukuba-shi, Ibaraki 305-0035 (JP)
• KAGEYAMA, Akira
Nilza-shi, Saitama 352-0034 (JP)

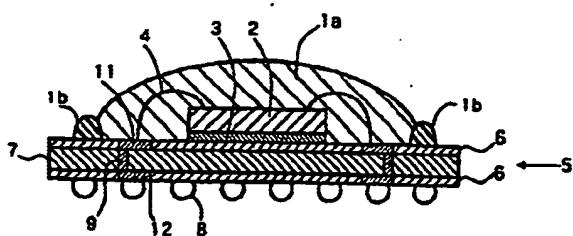
(74) Representative: Strehl Schübel-Hopf & Partner
Maximilianstrasse 54
80538 München (DE)

(54) PASTE COMPOSITION, AND PROTECTIVE FILM AND SEMICONDUCTOR DEVICE BOTH
OBTAINED WITH THE SAME

(57) A paste composition which comprises as essential ingredients (A) a thermoplastic resin, (B) an epoxy resin, (C) a coupling agent, (D) a powdery inorganic filler, (E) a powder having rubber elasticity and (F) an organic solvent and which, when applied and dried, gives a coating film having a void content of 3 % by volume or higher and a water vapor permeability as measured at

ured at 40°C and 90 %RH of 500 g/m².24h or less; a protective film which is formed by applying the paste composition to a surface of a semiconductor part and drying it and has a void content of 3 % by volume or higher and a water vapor permeability as measured at 40°C and 90 %RH of 500 g/m².24h or less; and a semiconductor device having the protective film.

FIG. 1



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